

BUK763R8-80E

N-channel TrenchMOS standard level FET

28 July 2016

Product data sheet

1. General description

Standard level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} rating of greater than 1 V at 175 °C

3. Applications

- 12V, 24V and 48V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- · Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	80	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	120	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	349	W
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 11		-	3.1	3.8	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 25 A; V _{DS} = 64 V; Fig. 13; Fig. 14		-	51	-	nC

[1] Continuous current is limited by package.



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Pinning information

Table 2. **Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D I
2	D	drain		
3	S	source		G TITA
mb	D	mounting base; connected to drain	1 3	mbb076 S
			D2PAK (SOT404)	

Ordering information

Table 3. **Ordering information**

Type number	Package				
	Name	Description	Version		
BUK763R8-80E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404		

Marking

Table 4. Marking codes

Type number	Marking code
BUK763R8-80E	BUK763R8-80E

Limiting values

Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	80	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω		-	80	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	349	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2</u>	[1]	-	120	Α
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 2</u>	[1]	-	120	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 3		-	778	Α
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C

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Symbol	Parameter	Conditions		Min	Max	Unit	
Source-drain	Source-drain diode						
Is	source current	T _{mb} = 25 °C	[1]	-	120	Α	
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	778	Α	
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 120 A; V_{sup} ≤ 80 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[2][3]	-	488	mJ	

- Continuous current is limited by package. Single-pulse avalanche rating limited by maximum junction temperature of 175 $^{\circ}\text{C}.$
- Refer to application note AN10273 for further information.

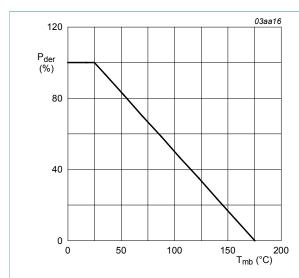


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

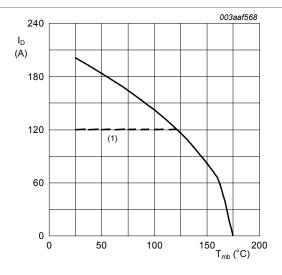


Fig. 2. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10V$

(1) Capped at 120 A due to package.

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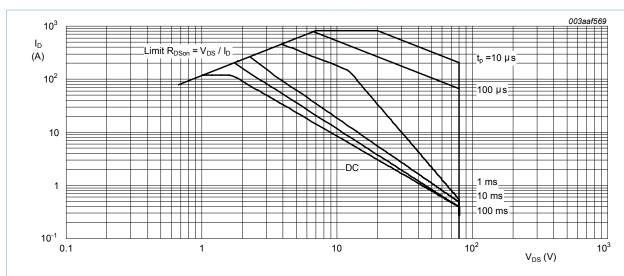
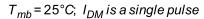


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



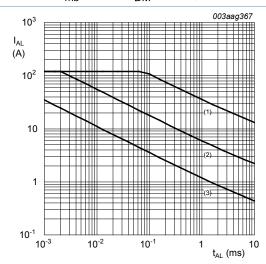


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time.

(1)
$$T_{j(init)} = 25$$
°C; (2) $T_{j(init)} = 150$ °C; (3) Repetitive Avalanche

9. Thermal characteristics

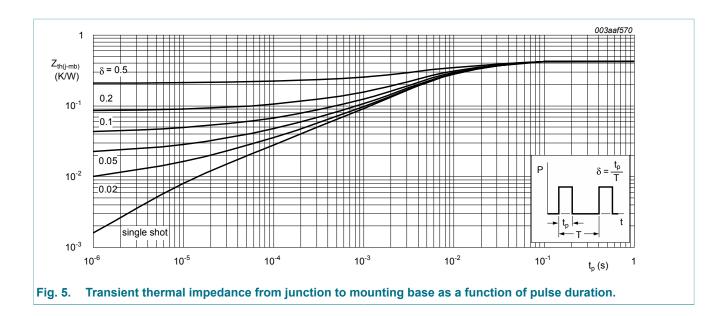
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	0.43	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Mir	Тур	Max	Unit	
Static chara	cteristics			·			
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	80	-	-	V	
	breakdown voltage	I _D = 250 mA; V _{GS} = 0 V; T _j = -55 °C	72	-	-	V	
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	2.4	. 3	4	V	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	1	-	-	V	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	4.5	V	
I _{DSS} drain leak	drain leakage current	V _{DS} = 80 V; V _{GS} = 0 V; T _j = 25 °C	-	0.15	1	μA	
		V _{DS} = 80 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA	
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	2	100	nA	
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA	
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	3.1	3.8	mΩ	
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 11	-	-	9.2	mΩ	
Dynamic characteristics							
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 64 V; V _{GS} = 10 V;	-	169	-	nC	
Q_{GS}	gate-source charge	Fig. 13; Fig. 14	-	37	-	nC	
Q_{GD}	gate-drain charge		-	51	-	nC	

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; <u>Fig. 15</u>		-	9020	12030	pF
C _{oss}	output capacitance			-	840	1010	pF
C _{rss}	reverse transfer capacitance			-	470	645	pF
t _{d(on)}	turn-on delay time	V_{DS} = 60 V; R_L = 2.4 Ω ; V_{GS} = 10 V;		-	38	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$		-	48	-	ns
$t_{d(off)}$	turn-off delay time	_		-	129	-	ns
t _f	fall time			-	65	-	ns
L _D	internal drain inductance	from upper edge of mounting base to centre of die		-	2.5	-	nH
L _S	internal source inductance	measured from source lead to source bond pad; T_j = 25 °C		-	7.5	-	nΗ
Source-dra	in diode		l				
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 ^{\circ}\text{C}$; Fig. 16		-	0.77	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	58	-	ns
Q _r	recovered charge	V _{DS} = 25 V		-	121	-	nC

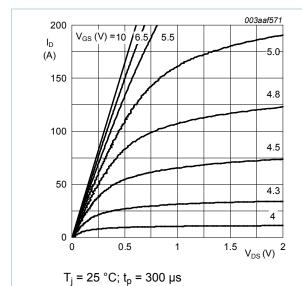


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

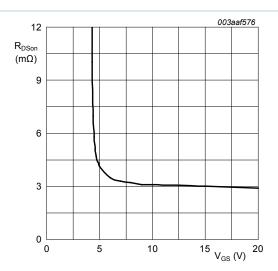


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values $T_j = 25 \,^{\circ}C; I_D = 25A$

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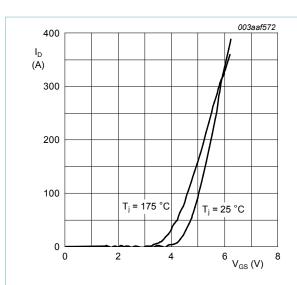


Fig. 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values



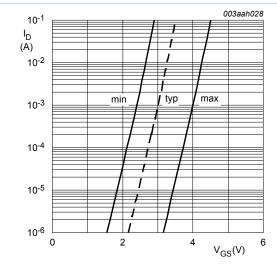


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

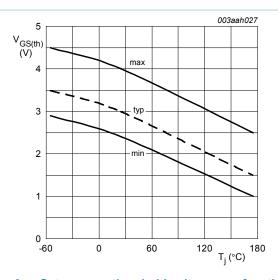
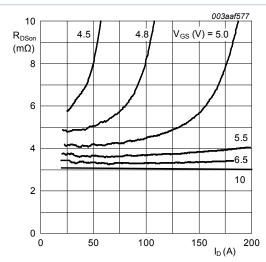


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D$$
 = 1 mA; V_{DS} = V_{GS}



 T_i = 25 °C; t_p = 300 μ s

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

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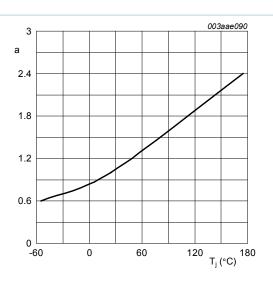


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

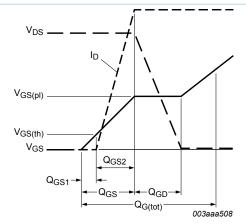
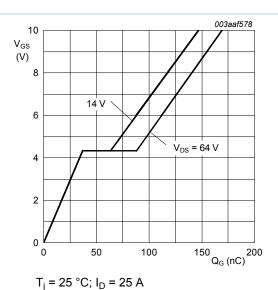
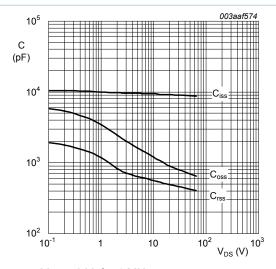


Fig. 14. Gate charge waveform definitions



1₁ - 20 0, 1₀ - 20 A

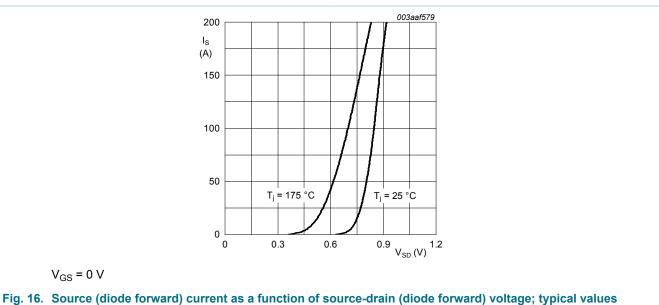
Fig. 13. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0 V$; f = 1 MHz

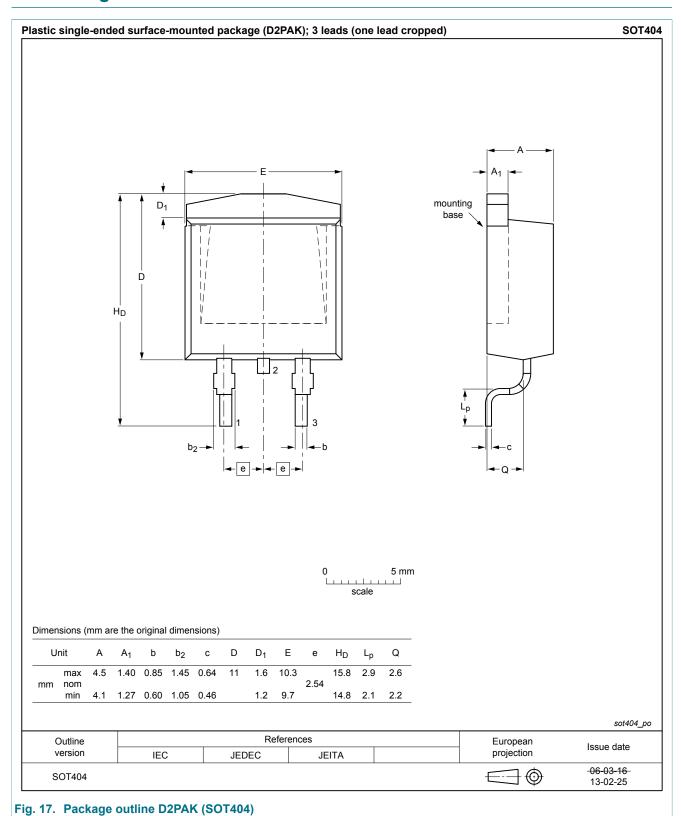
Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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11. Package outline



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12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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